● General Description

The TF020N025NG combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$ .This device is ideal for load switch and battery protection applications.

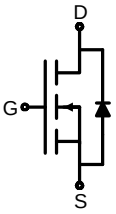
● Features

Advance high cell density Trench technology
Low $R_{DS(ON)}$ to minimize conductive loss
Low Gate Charge for fast switching
Low Thermal resistance

●Application

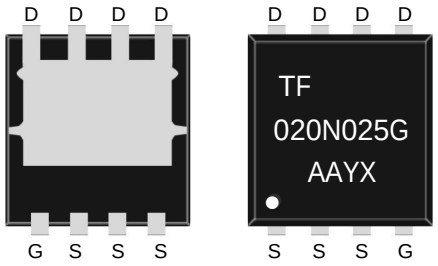
MB/VGA Vcore
SMPS 2nd Synchronous Rectifier
POL application
BLDC Motor driver

● Product Summary



V_{DS} =25V I_D=100A
$R_{DSON(4.5V\ typ)}$ =2.0mΩ
$R_{DSON(2.5V\ typ)}$ =3.9mΩ

RoHS compliant



PDFNWB5x6-8L

●Ordering Information:

Part NO.	TF020N025NG
Marking 1	020N025G: TF020N025NG
Marking 2	TF:tuofeng; AA:device code; Y:year code; X:Week
MOQ	5000

●Absolute Maximum Ratings (T_C =25℃)

Parameter	**Symbol**	Rating	Unit
Drain-Source Voltage	V_{DS}	25	V
Gate-Source Voltage	V_{GS}	±12	V
Continuous Drain Current	$I_{D@}T_C$=25℃	110	A
	$I_{D@}T_C$=75℃	70	A
	$I_{D\ @}T_C$=100℃	60	A
Pulsed Drain Current ①	I_{DM}	200	A
Total Power Dissipation	$P_D@T_C$=25℃	65	W
Total Power Dissipation	$P_D@T_A$=25℃	1.0	W
Operating Junction Temperature	T_J	-55 to 150	℃
Storage Temperature	T_{STG}	-55 to 150	℃

Note: ① Pulse Test : Pulse width ≤ 300μs, Duty cycle ≤ 2% ;

Single Pulse Avalanche Energy	E_{AS}	75	mJ
Avalanche Current	I_{AS} I_{AR}	25	A

●Thermal resistance

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case	R_{thJC}	-	-	2.2	°C/W
Thermal resistance, junction - ambient	R_{thJA}	-	-	55	°C/W
Soldering temperature, wave soldering for 8s	T_{sold}	-	-	265	°C

●Electronic Characteristics(T_a = 25℃)

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS} =0V,I_D =250uA	25			V
Gate Threshold Voltage	$V_{GS(TH)}$	V_{GS} =V_{DS}, I_D =250uA	0.5	1.0	1.5	V
Drain-Source Leakage Current	I_{DSS}	V_{DS}=25V, V_{GS} =0V			1.0	uA
Gate- Source Leakage Current	I_{GSS}	V_{GS}=±12V ,V_{DS} =0V			±100	nA
Static Drain-source On Resistance	$R_{DS(ON)}$	V_{GS}=4.5V, I_D=20A		2.0	3.0	mΩ
		V_{GS}=2.5V, I_D=20A		3.9	5.5	mΩ
Forward Transconductance	g_{FS}	V_{DS} =25V, I_D=20A		10		S
Source-drain voltage	V_{SD}	Is=20A			1.20	V

●Electronic Characteristics(T_a = 25℃)

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Input capacitance	Ciss	Vds=15V,Vgs=0V f = 1MHz	-	3611	-	pF
Output capacitance	Coss		-	1856	-	
Reverse transfer capacitance	Crss		-	73	-	

●Gate Charge characteristics(T_a = 25℃)

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Gate Risistance	R_g	f = 1MHz		1.5		Ω
Total gate charge	Qg	V_{DD} = 15V	-	28.18	-	nC
Gate - Source charge	Qgs	I_D = 20A	-	5.6	-	
Gate - Drain charge	Qgd	V_{GS} = 4.5V	-	6.6	-	
Turn-ON Delay time	$t_{D(on)}$	V_{GS}=4.5V ,V_{DS}=15V R_G =3.0Ω, I=20A		12.8		ns
Turn-ON Rise time	t_r			4.00		ns
Turn-Off Delay time	$t_{D(off)}$			32.0		ns
Turn-Off Fall time	t_f			8.00		ns

Figure 1 Output Characteristics

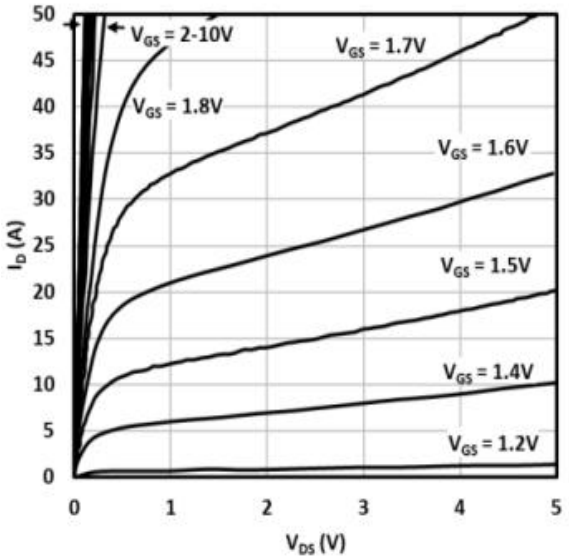


Figure 2 Transfer Characteristics

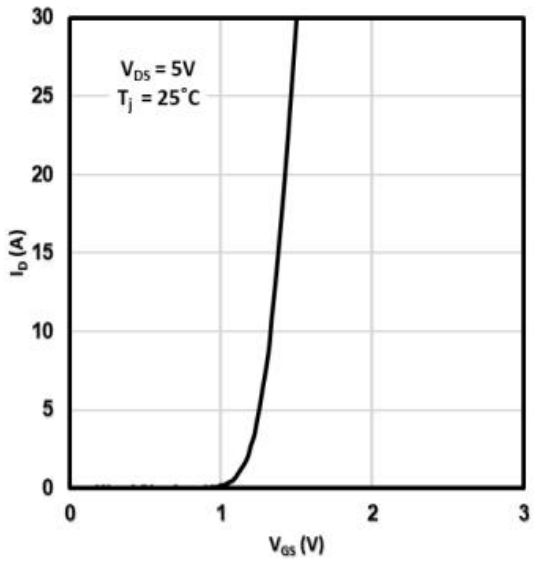


Figure 3 On-resistance vs.gate voltage

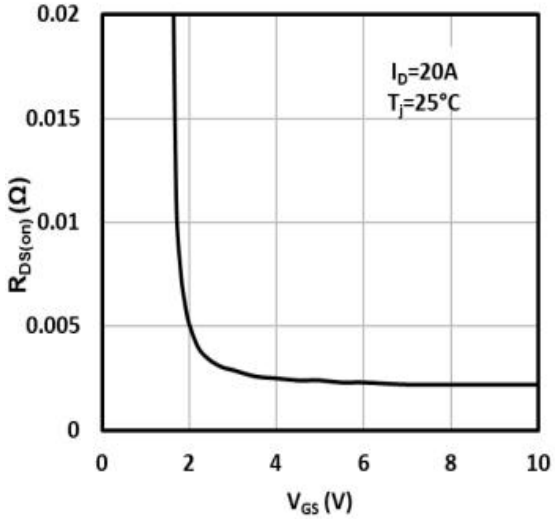


Figure 4 On-resistance vs.drain current

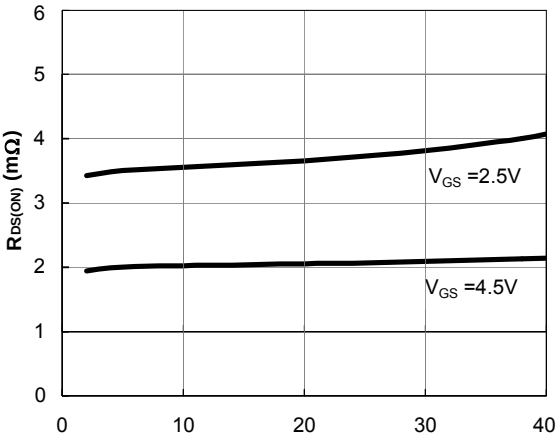


Figure 5 Source-to-drain diode forwrd characteristics

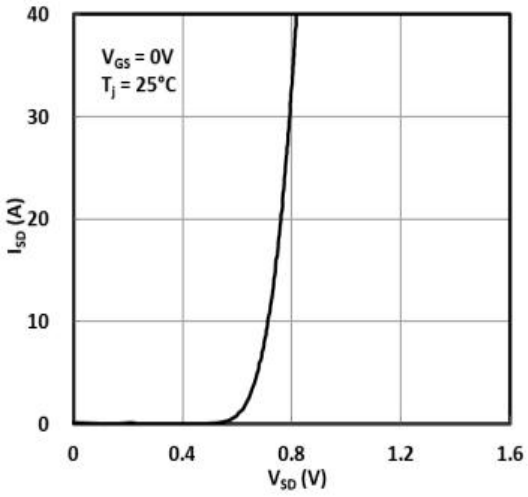


Figure 6 Capacitance vs drain-to-source Voltage

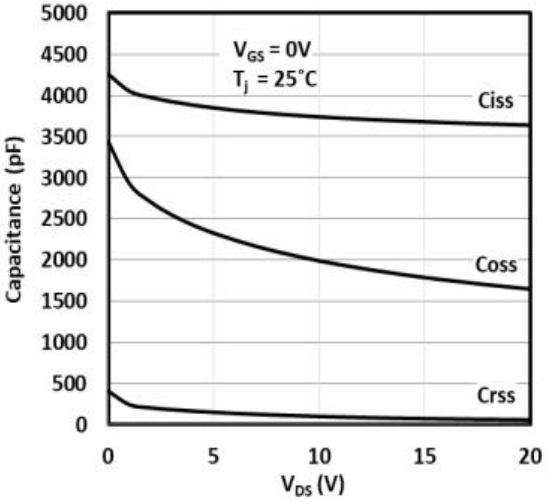


Figure 7 Gate-to-source voltage vs.gate charge

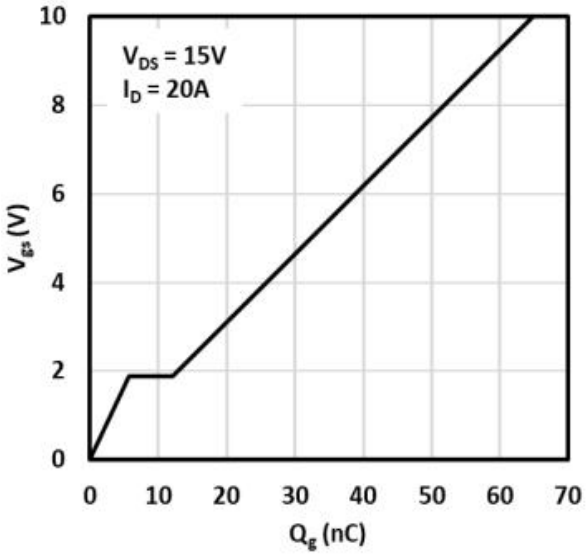


Figure 8 Maximum drain current vs.case temperature

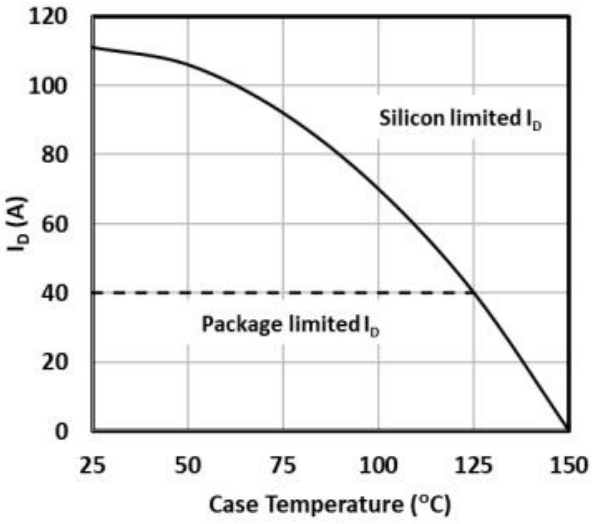
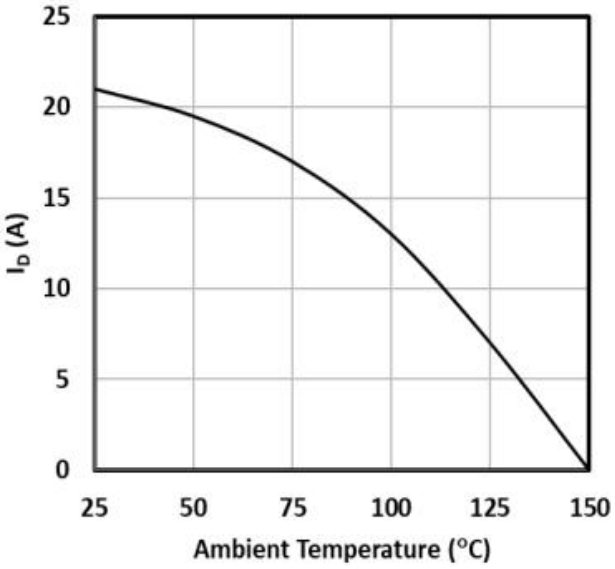
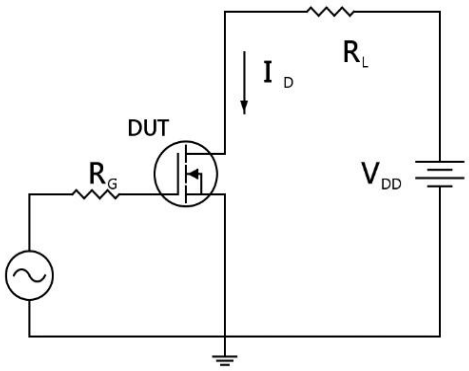
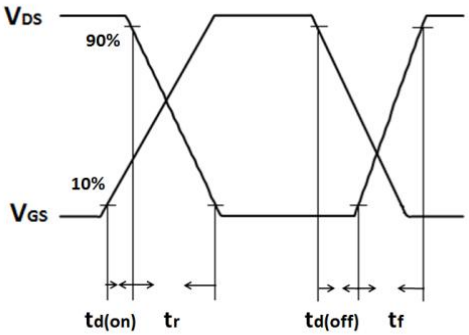


Figure 9 Maximum drain current vs. ambient temperature

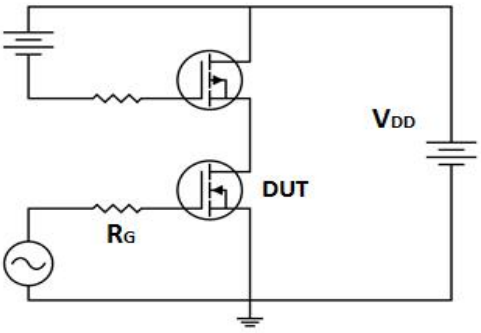


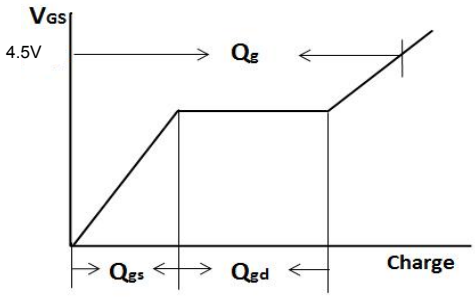
Resistive switching time test circuit &waveforms



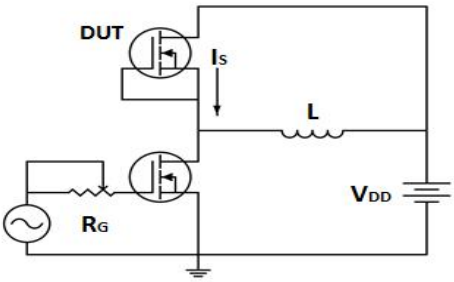


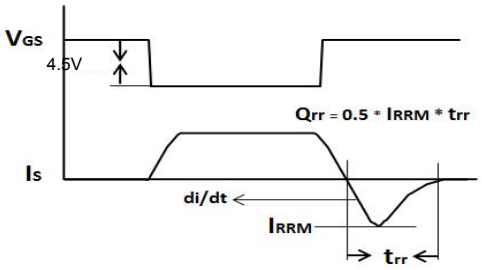
Gate charge test circuit &waveforms



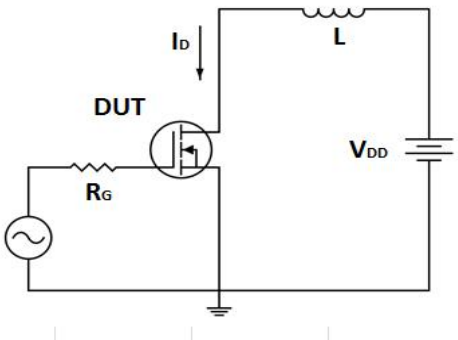


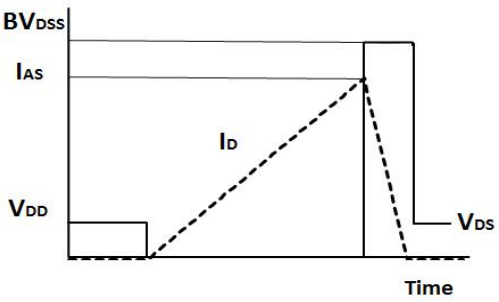
Peak diode recovery dv/dt circuit &waveforms



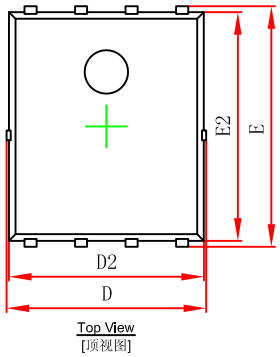


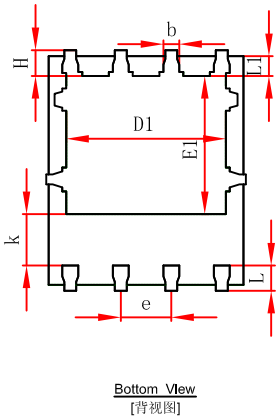
Unclamped inductive switching test circuit &waveforms

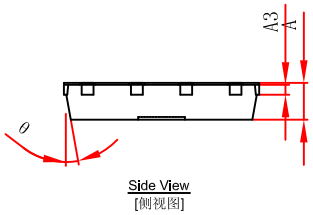




PDFNWB5x6-8L Package Outline Dimensions

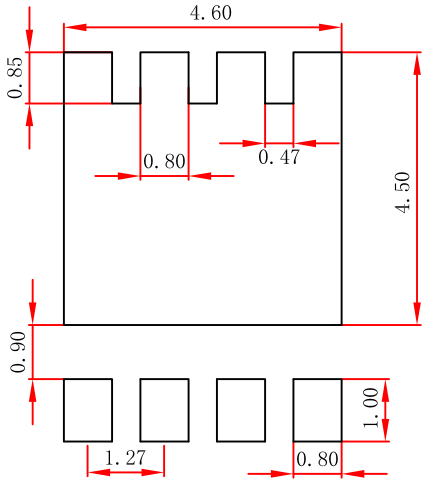






Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.000	0.035	0.039
A3	0.254REF.		0.010REF.	
D	4.944	5.096	0.195	0.201
E	5.974	6.126	0.235	0.241
D1	3.910	4.110	0.154	0.162
E1	3.375	3.575	0.133	0.141
D2	4.824	4.976	0.190	0.196
E2	5.674	5.826	0.223	0.229
k	1.190	1.390	0.047	0.055
b	0.350	0.450	0.014	0.018
e	1.270TYP.		0.050TYP.	
L	0.559	0.711	0.022	0.028
L1	0.424	0.576	0.017	0.023
H	0.574	0.726	0.023	0.029
θ	10°	12°	10°	12°

PDFNWB5x6-8L Suggested Pad Layout



Note:
1.Controlling dimension:in millimeters.
2.General tolerance:±0.05mm.
3.The pad layout is for reference purposes only.